Vishay Semiconductors

Hyperfast Rectifier, 3 A FRED Pt[®]

Cathode

3 A

100 V

0.69 V

25 ns

175 °C

SMC (DO-214AB)

Single

Anode



• Hyperfast recovery time, reduced Qrr, and soft recoverv



HALOGEN

- 175 °C maximum operating junction temperature
- · Specified for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element.

MECHANICAL DATA

Case: SMC (DO-214AB)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		100	V			
Average rectified forward current	I _{F(AV)}	T _{Sp} = 142 °C	3	٨			
Non-repetitive peak surge current	I _{FSM}	$T_J = 25 \ ^{\circ}C$, 6 ms square pulse	130	A			
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	100	-	-		
Forward voltage, per diode	V _F	I _F = 3 A	-	0.83	0.90	V	
		I _F = 3 A, T _J = 125 °C	-	0.69	0.75		
Reverse leakage current, per diode	I _R	V _R = V _R rated	-	-	2		
		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1	10	μA	
Junction capacitance	CT	V _R = 100 V	-	23	-	pF	

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FREE



SMC (DO-214AB)

I_{F(AV)}

 V_R

V_F at I_F

t_{rr} T_{.1} max.

Package

Circuit configuration

30

3D Models

LINKS TO ADDITIONAL RESOURCES

PRIMARY CHARACTERISTICS



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ J}$	-	27	-		
Bayaraa raaayan tima	t _{rr}	I _F = 0.5 A, I _R = 1 A, I	-	-	25		
Reverse recovery time		T _J = 25 °C		-	18	-	ns
		T _J = 125 °C		-	30	-	
Deals reactions ourrent	I _{RRM}	T _J = 25 °C	I _F = 3 A, dI _F /dt = 200 A/µs, V _B = 160 V	-	2.1	-	A nC
Peak recovery current		T _J = 125 °C		-	4	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C	VR - 100 V	-	19	-	
		T _J = 125 °C		-	60	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to mount	R _{thJM}	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	7.7	14	°C/W
Approvimate weight				0.24		g
Approximate weight				0.008		oz.
Marking device		Case style SMC (DO-214AB)	3H1			



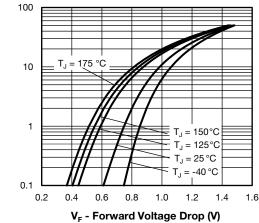


Fig. 1 - Typical Forward Voltage Drop Characteristics

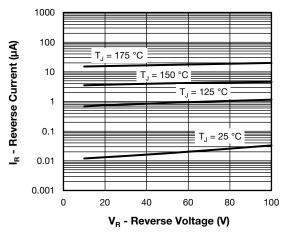
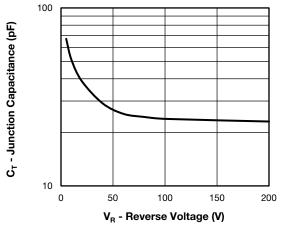


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

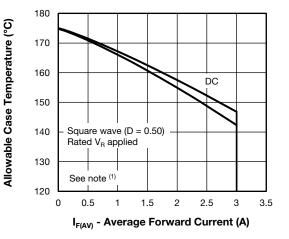


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

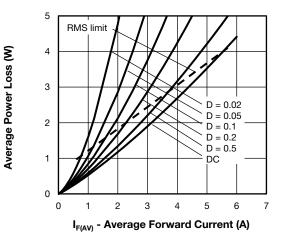


Fig. 5 - Forward Power Loss Characteristics

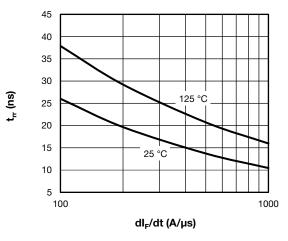
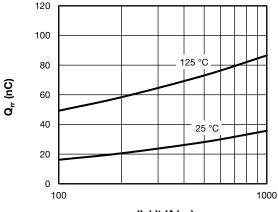


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt



dl_F/dt (A/µs)

Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \, x \, \mathsf{V_{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \, x \, \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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VS-3ECH01-M3

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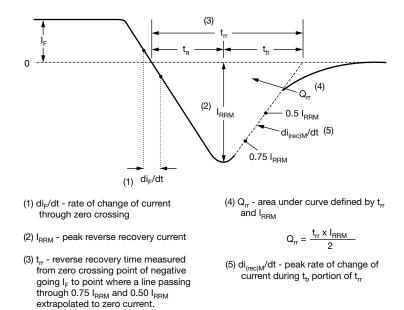


Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

SHAY

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		1					
Device code	VS-	3	Е	с	н	01	-МЗ
		2	3	4	5	6	7
	1	- Vis	hay Sen	nicondu	ctors pro	oduct	
	2	- Cur	rent cod	le (3 = 3	5 A)		
	3	- Circ	cuit conf	iguratio	ר:		
		E =	single c	liode			
	4	- C =	SMC pa	ackage			
	5	- Pro	cess typ	e,			
		H =	hyperfa	st recov	very		
	6	- Vol	tage coo	de (01 =	100 V)		
	7	M3	8 = halog	gen-free	, RoHS-	complia	ant, and

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-3ECH01-M3/9AT	3500	3500	13"diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95402				
Part marking information	www.vishay.com/doc?95472			
Packaging information	www.vishay.com/doc?95404			

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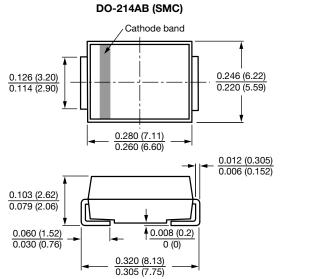


Outline Dimensions

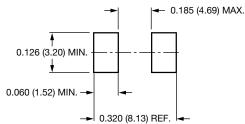
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SMC

DIMENSIONS in inches (millimeters)



Mounting Pad Layout





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